

MOSFETs Silicon N-channel MOS (U-MOS X-H)

TPN19008QM

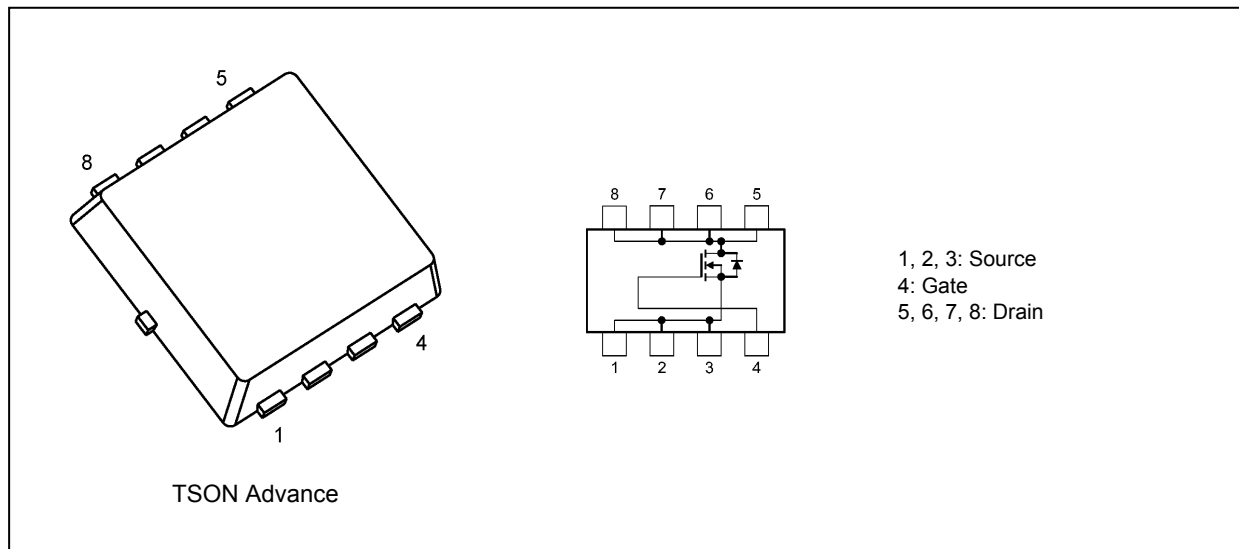
1. Applications

- High-Efficiency DC-DC Converters
- Switching Voltage Regulators
- Motor Drivers

2. Features

- (1) High-speed switching
- (2) Small gate charge: $Q_{SW} = 5.5 \text{ nC}$ (typ.)
- (3) Small output charge: $Q_{OSS} = 16.5 \text{ nC}$ (typ.)
- (4) Low drain-source on-resistance: $R_{DS(ON)} = 14.7 \text{ m}\Omega$ (typ.) ($V_{GS} = 10 \text{ V}$)
- (5) Low leakage current: $I_{DSS} = 10 \text{ }\mu\text{A}$ (max) ($V_{DS} = 80 \text{ V}$)
- (6) Enhancement mode: $V_{th} = 2.5 \text{ to } 3.5 \text{ V}$ ($V_{DS} = 10 \text{ V}$, $I_D = 0.2 \text{ mA}$)

3. Packaging and Internal Circuit



Start of commercial production

2019-09

4. Absolute Maximum Ratings (Note) ($T_a = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

| Characteristics | Symbol | Rating | Unit |
|--------------------------------------------------------------------|-----------|------------|--------------------|
| Drain-source voltage | V_{DS} | 80 | V |
| Gate-source voltage | V_{GS} | ± 20 | |
| Drain current (DC) ($T_c = 25\text{ }^{\circ}\text{C}$) (Note 1) | I_D | 34 | A |
| Drain current (DC) (Silicon limit) (Note 1), (Note 2) | | 38 | |
| Drain current (pulsed) ($t = 100\text{ }\mu\text{s}$) (Note 1) | I_{DP} | 95 | |
| Power dissipation ($T_c = 25\text{ }^{\circ}\text{C}$) | P_D | 57 | W |
| Power dissipation (Note 3) | | 2.67 | |
| Power dissipation (Note 4) | | 0.63 | |
| Single-pulse avalanche energy (Note 5) | E_{AS} | 9.16 | mJ |
| Single-pulse avalanche current (Note 5) | I_{AS} | 34 | A |
| Channel temperature | T_{ch} | 175 | $^{\circ}\text{C}$ |
| Storage temperature | T_{stg} | -55 to 175 | |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

| Characteristics | Symbol | Max | Unit |
|---------------------------------------------------------------------------------------|----------------|-----|----------------------|
| Channel-to-case thermal resistance ($T_c = 25\text{ }^{\circ}\text{C}$) | $R_{th(ch-c)}$ | 2.6 | $^{\circ}\text{C/W}$ |
| Channel-to-ambient thermal resistance ($T_a = 25\text{ }^{\circ}\text{C}$) (Note 3) | $R_{th(ch-a)}$ | 56 | |
| Channel-to-ambient thermal resistance ($T_a = 25\text{ }^{\circ}\text{C}$) (Note 4) | $R_{th(ch-a)}$ | 235 | |

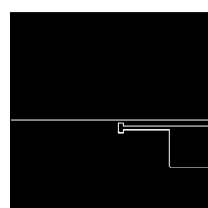
Note 1: Ensure that the channel temperature does not exceed $175\text{ }^{\circ}\text{C}$.

Note 2: Limited by silicon chip capability.

Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1

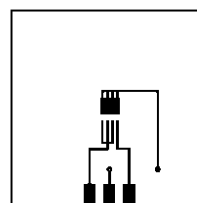
Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 5: $V_{DD} = 64\text{ V}$, $T_{ch} = 25\text{ }^{\circ}\text{C}$ (initial), $L = 6.1\text{ }\mu\text{H}$, $I_{AS} = 34\text{ A}$



FR-4
25.4 × 25.4 × 1.6
(Unit: mm)
2 oz copper

Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)



FR-4
25.4 × 25.4 × 1.6
(Unit: mm)
2 oz copper

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

6.1. Static Characteristics ($T_a = 25^\circ\text{C}$ unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Typ. | Max | Unit |
|-----------------------------------------|---------------|-------------------------------------------------|-----|------|-----------|------------------|
| Gate leakage current | I_{GSS} | $V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$ | — | — | ± 0.1 | μA |
| Drain cut-off current | I_{DSS} | $V_{DS} = 80\text{ V}, V_{GS} = 0\text{ V}$ | — | — | 10 | |
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | $I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$ | 80 | — | — | V |
| Drain-source breakdown voltage (Note 6) | $V_{(BR)DSX}$ | $I_D = 10\text{ mA}, V_{GS} = -20\text{ V}$ | 60 | — | — | |
| Gate threshold voltage | V_{th} | $V_{DS} = 10\text{ V}, I_D = 0.2\text{ mA}$ | 2.5 | — | 3.5 | |
| Drain-source on-resistance | $R_{DS(ON)}$ | $V_{GS} = 6\text{ V}, I_D = 13\text{ A}$ | — | 20 | 28 | $\text{m}\Omega$ |
| | | $V_{GS} = 10\text{ V}, I_D = 17\text{ A}$ | — | 14.7 | 19 | |

Note 6: If a reverse bias is applied between gate and source, this device enters $V_{(BR)DSX}$ mode. Note that the drain-source breakdown voltage is lowered in this mode.

6.2. Dynamic Characteristics ($T_a = 25^\circ\text{C}$ unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Typ. | Max | Unit |
|--------------------------------|-----------|---------------------------------------------------------------|-----|------|------|-------------|
| Input capacitance | C_{iss} | $V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$ | — | 1020 | 1450 | pF |
| Reverse transfer capacitance | C_{rss} | | — | 15 | 50 | |
| Output capacitance | C_{oss} | | — | 250 | — | |
| Gate resistance | r_g | — | — | 1.6 | 2.4 | Ω |
| Switching time (rise time) | t_r | See Fig. 6.2.1 | — | 7.7 | — | ns |
| Switching time (turn-on time) | t_{on} | | — | 17 | — | |
| Switching time (fall time) | t_f | | — | 5 | — | |
| Switching time (turn-off time) | t_{off} | | — | 20 | — | |

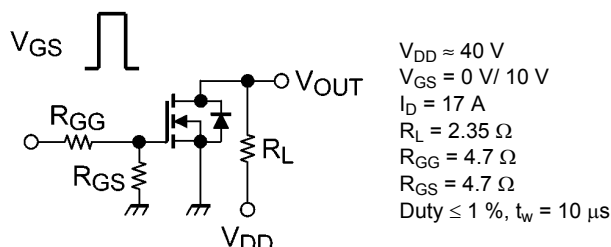


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25^\circ\text{C}$ unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Typ. | Max | Unit |
|-------------------------------------------------|-----------|-----------------------------------------------------------------------|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | Q_g | $V_{DD} \approx 40\text{ V}, V_{GS} = 10\text{ V}, I_D = 17\text{ A}$ | — | 16 | — | nC |
| | | $V_{DD} \approx 40\text{ V}, V_{GS} = 6\text{ V}, I_D = 13\text{ A}$ | — | 9.7 | — | |
| Gate-source charge 1 | Q_{gs1} | $V_{DD} \approx 40\text{ V}, V_{GS} = 10\text{ V}, I_D = 17\text{ A}$ | — | 4.9 | — | |
| Gate-drain charge | Q_{gd} | | — | 3.8 | — | |
| Gate switch charge | Q_{SW} | | — | 5.5 | — | |
| Output charge | Q_{oss} | $V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$ | — | 16.5 | — | |

6.4. Source-Drain Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Typ. | Max | Unit |
|-----------------------------------------|----------------------------------|------------------------------------------------------------------------------------------------------------|-----|------|------|------|
| Reverse drain current (pulsed) (Note 7) | I _{DRP} (t = 100 μs) | — | — | — | 95 | A |
| Diode forward voltage | V _{DSF} | I _{DR} = 34 A, V _{GS} = 0 V | — | — | -1.2 | V |
| Reverse recovery time | t _{rr} | V _R = 40 V, I _{DR} = 8.5 A, V _{GS} = 0 V, -dI _{DR} /dt = 100 A/μs | — | 32 | — | ns |
| Reverse recovery charge | Q _{rr} | | — | 26 | — | nC |

Note 7: Ensure that the channel temperature does not exceed 175 °C.

7. Marking

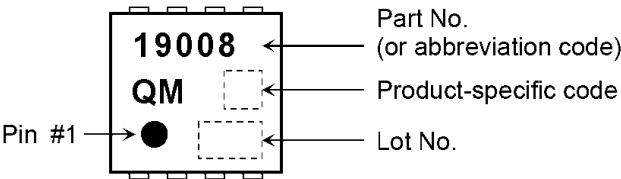


Fig. 7.1 Marking

8. Characteristics Curves (Note)

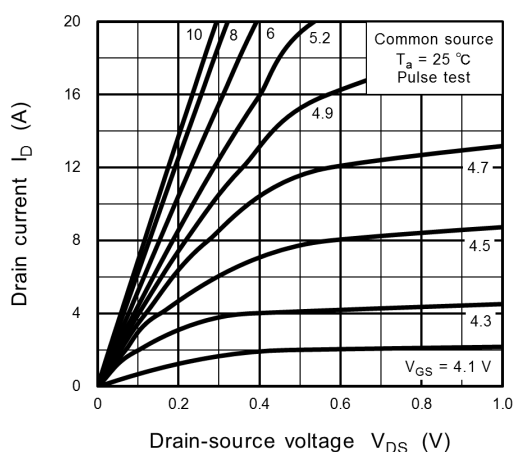


Fig. 8.1 $I_D - V_{DS}$

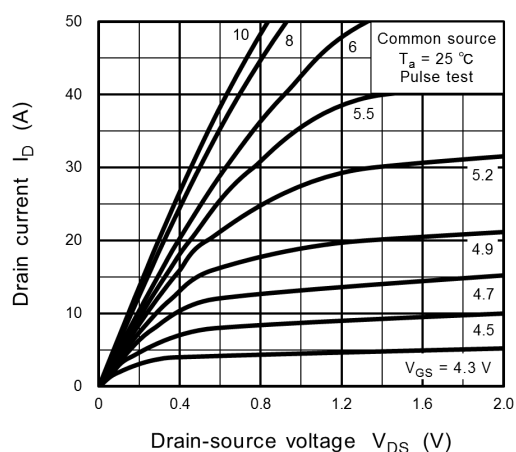


Fig. 8.2 $I_D - V_{DS}$

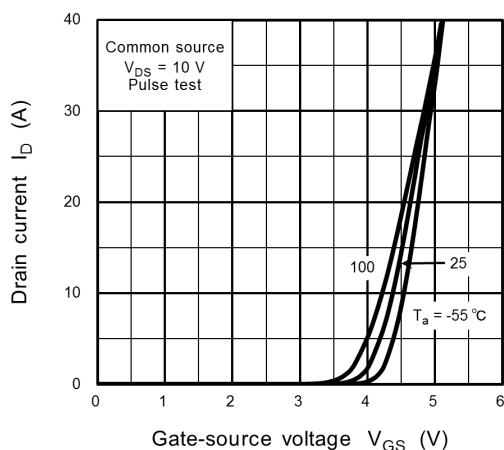


Fig. 8.3 $I_D - V_{GS}$

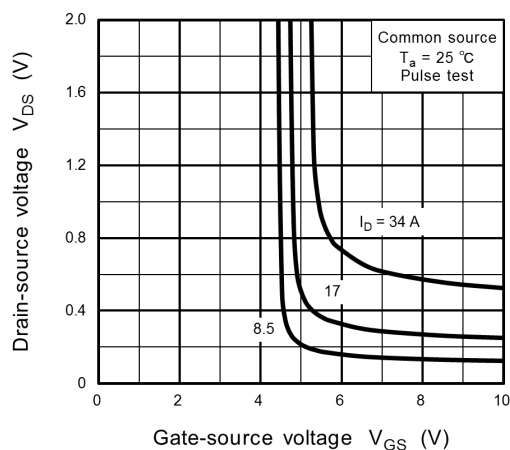


Fig. 8.4 $V_{DS} - V_{GS}$

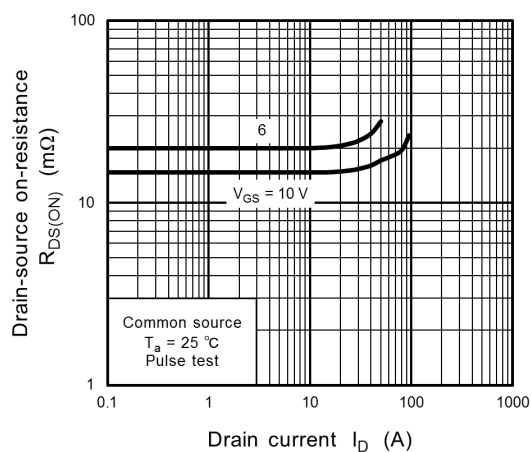


Fig. 8.5 $R_{DS(ON)} - I_D$

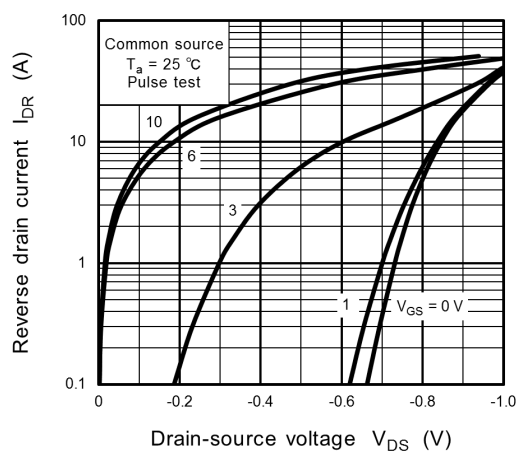


Fig. 8.6 $I_{DR} - V_{DS}$

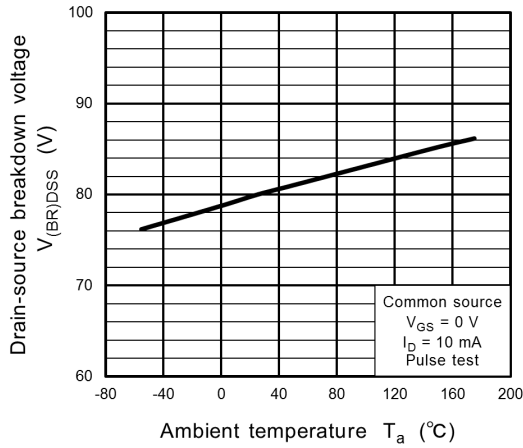


Fig. 8.7 $V_{(BR)DSS} - T_a$

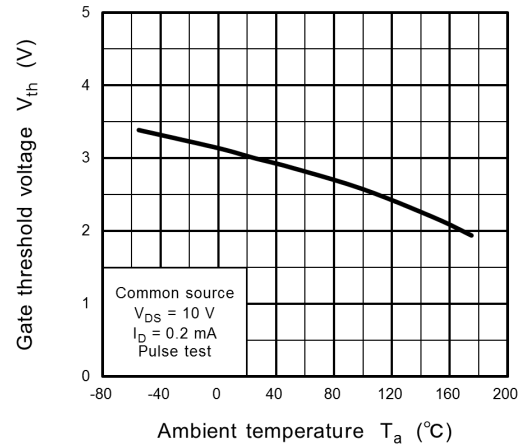


Fig. 8.8 $V_{th} - T_a$

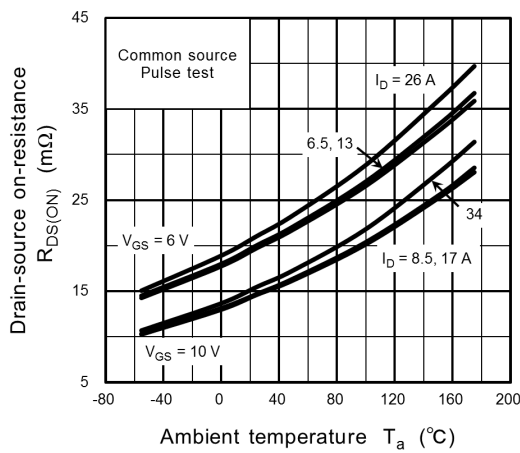


Fig. 8.9 $R_{DS(ON)} - T_a$

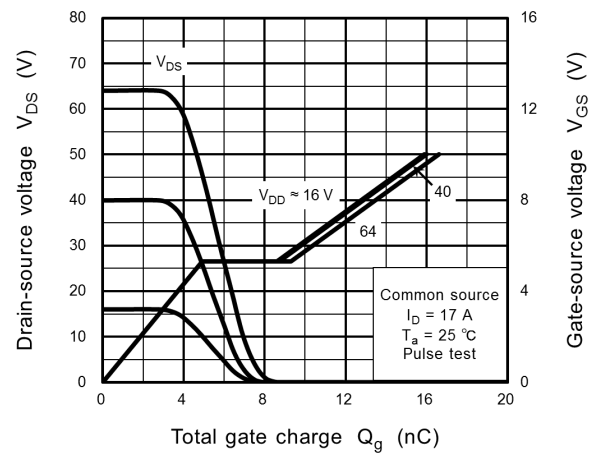


Fig. 8.10 Dynamic Input/Output Characteristics

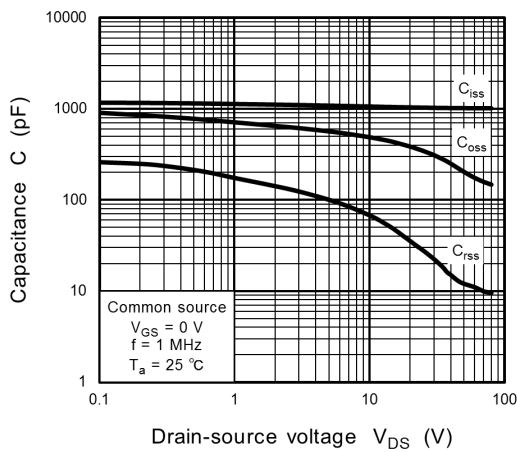


Fig. 8.11 Capacitance - V_{DS}

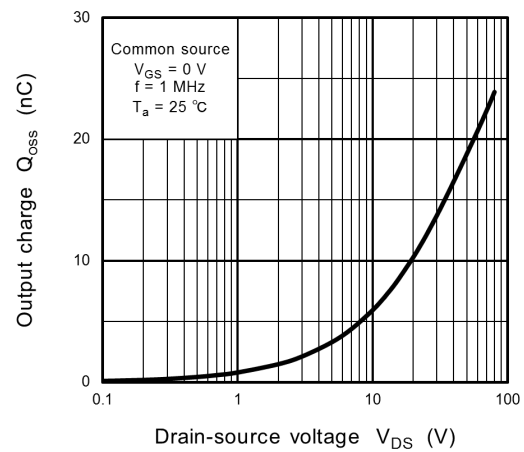


Fig. 8.12 $Q_{oss} - V_{DS}$

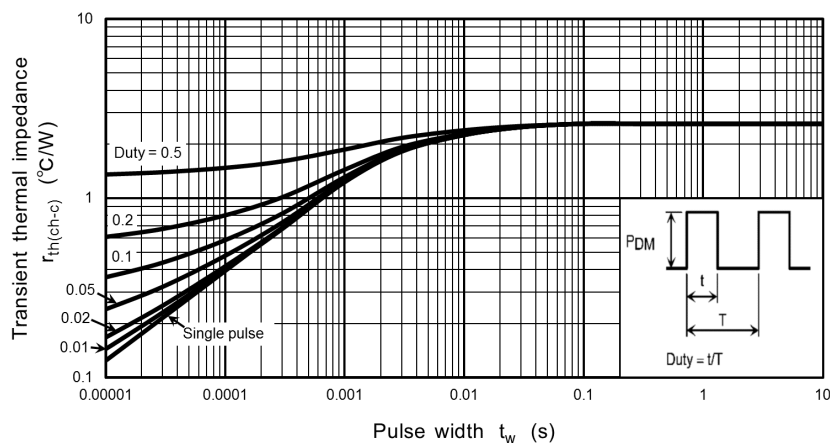


Fig. 8.13 $r_{th} - t_w$
(Guaranteed Maximum)

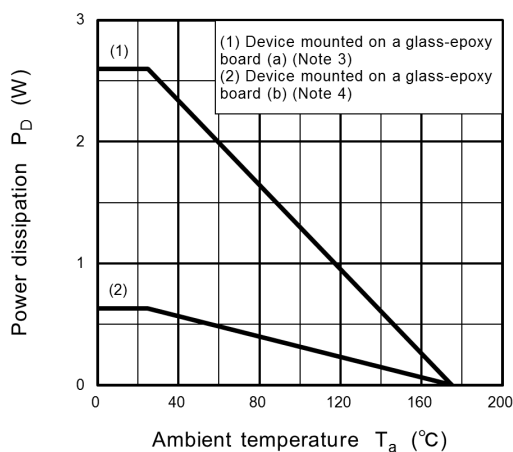


Fig. 8.14 $P_D - T_a$
(Guaranteed Maximum)

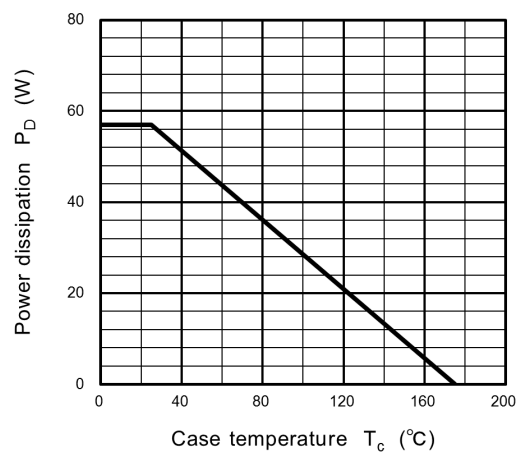


Fig. 8.15 $P_D - T_c$
(Guaranteed Maximum)

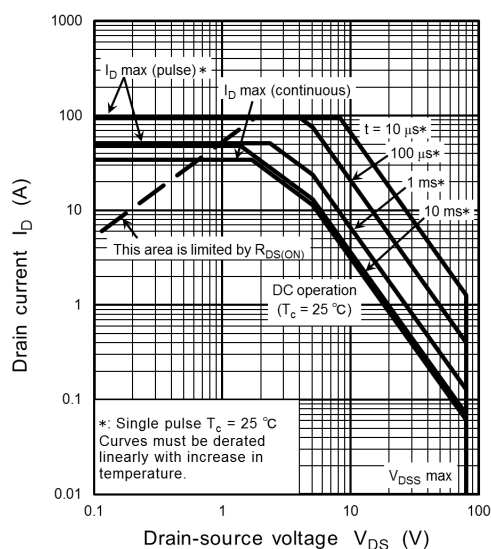
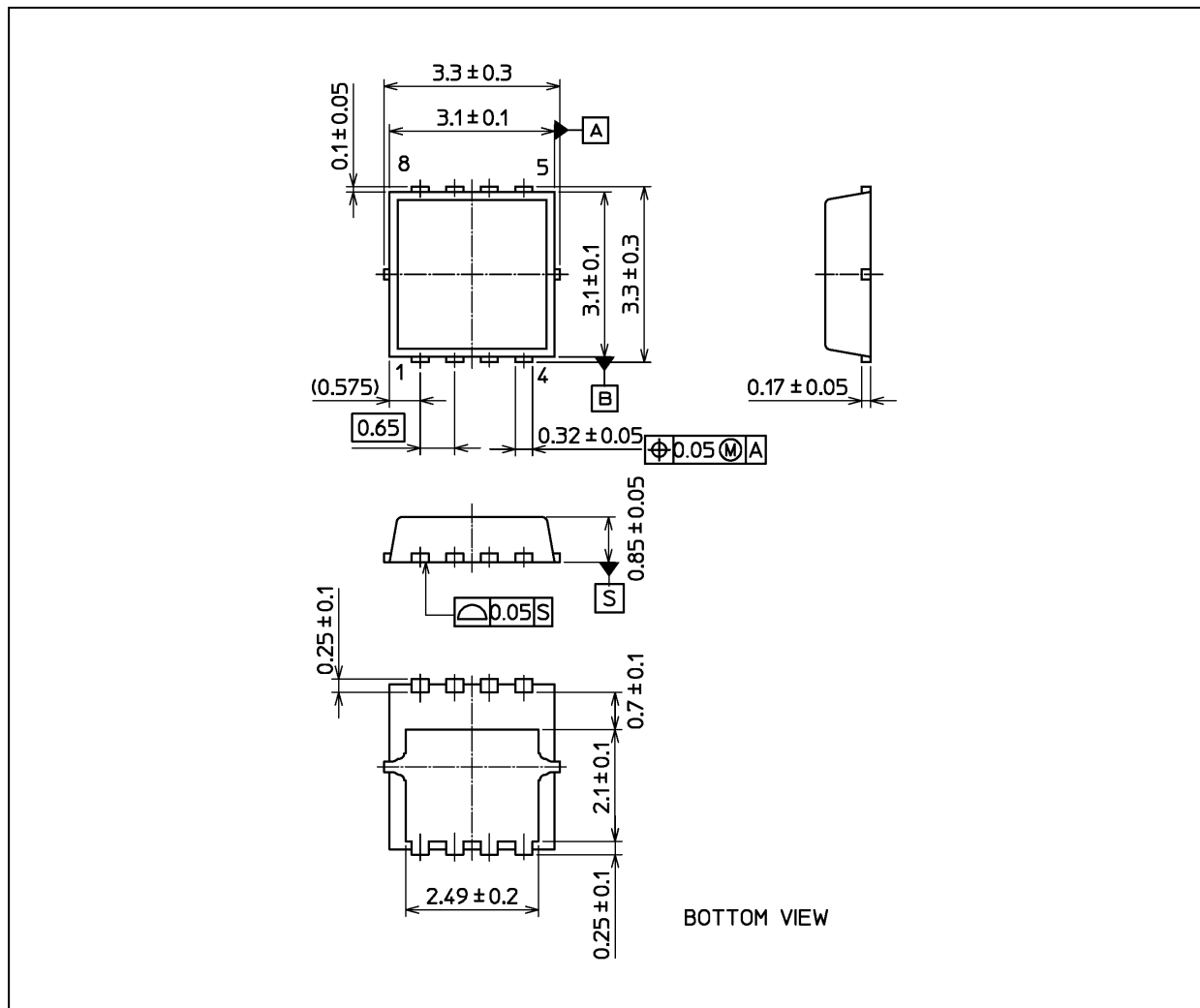


Fig. 8.16 Safe Operating Area
(Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Package Dimensions

Unit: mm



Weight: 0.02 g (typ.)

| Package Name(s) |
|------------------------|
| TOSHIBA: 2-3X1S |
| Nickname: TSON Advance |

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